# 1. General description

PNP high-voltage low  $V_{CEsat}$  transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

### 2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- Qualified according to AEC-Q101 and recommended for use in automotive applications

# 3. Applications

- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Switch Mode Power Supply (SMPS)

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-140	V
Ic	collector current		-	-	-4	Α
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	-10	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	100	150	mΩ

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	C
2	С	collector		В
3	Е	emitter		
4	С	collector	□1 □2 □3	Ė
			SC-73 (SOT223)	sym028



## 140 V, 4 A PNP high-voltage low VCEsat transistor

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package						
	Name	Description	Version				
PBHV9414Z-Q		plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223				

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PBHV9414Z-Q	V9414Z

# 8. Limiting values

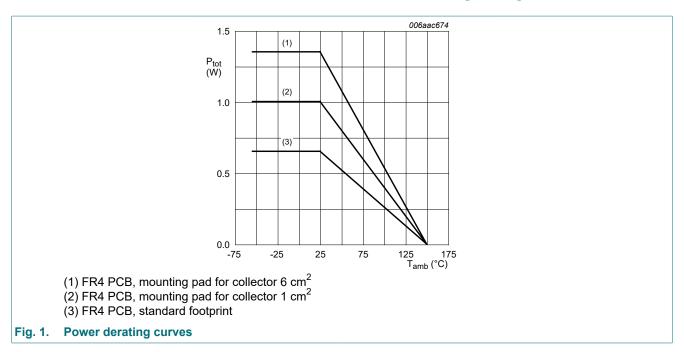
#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-180	V
$V_{CEO}$	collector-emitter voltage	open base		-	-140	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-7	V
I <sub>C</sub>	collector current			-	-4	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-10	Α
I <sub>B</sub>	base current			-	-500	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.65	W
			[2]	-	1	W
			[3]	-	1.35	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>. Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

#### 140 V, 4 A PNP high-voltage low VCEsat transistor

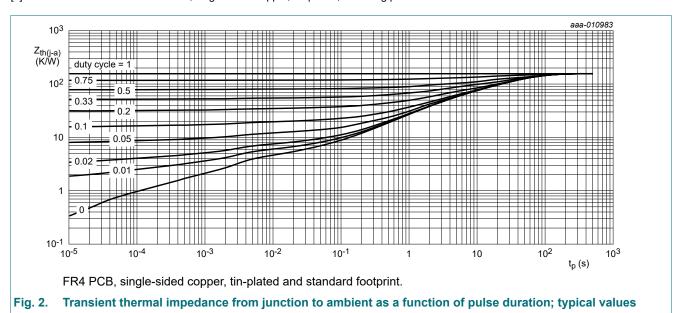


## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	thermal resistance from	in free air	[1]	-	-	192	K/W
		[2]	-	-	125	K/W	
			[3]	-	-	93	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	16	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>. Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



#### 140 V, 4 A PNP high-voltage low VCEsat transistor

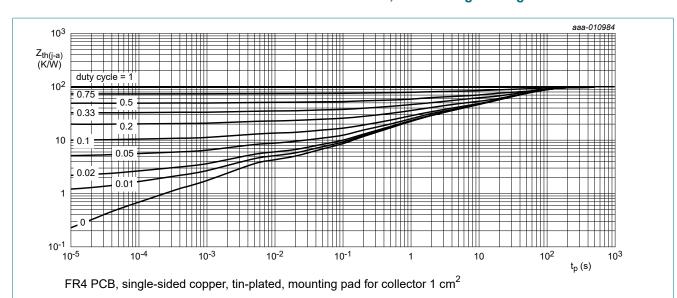


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

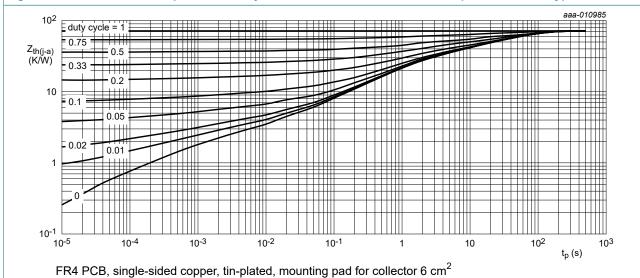


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 140 V, 4 A PNP high-voltage low VCEsat transistor

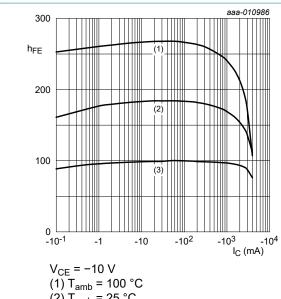
# 10. Characteristics

## **Table 7. Characteristics**

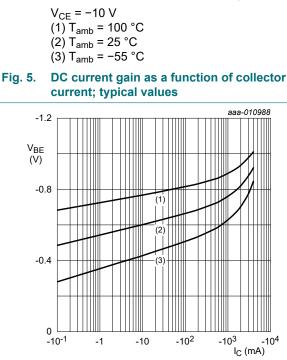
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>СВО</sub>	collector-base cut-off	V <sub>CB</sub> = -150 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -150 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -6 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -115 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -10 mA; T <sub>amb</sub> = 25 °C	100	160	-	
		$V_{CE}$ = -5 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	100	150	300	
		$V_{CE}$ = -5 V; $I_{C}$ = -3 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	75	100	-	
		$V_{CE}$ = -5 V; $I_{C}$ = -4 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	35	50	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -100 mA; $I_B$ = -5 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-45	-60	mV
		$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-60	-100	mV
		$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-100	-150	mV
		$I_C$ = -3 A; $I_B$ = -300 mA; $t_p \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C; pulsed	-	-275	-370	mV
		$I_C$ = -4 A; $I_B$ = -400 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	-420	-550	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	100	150	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage		-	-	-1.2	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = -5 V; $I_{C}$ = -1 A; $t_{p}$ ≤ 300 μs; pulsed; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.1	V

**PBHV9414Z-Q Nexperia** 

#### 140 V, 4 A PNP high-voltage low VCEsat transistor



current; typical values



 $V_{CE} = -10 \text{ V}$ (1)  $T_{amb} = -55$  °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 7. Base-emitter voltage as a function of collector current; typical values

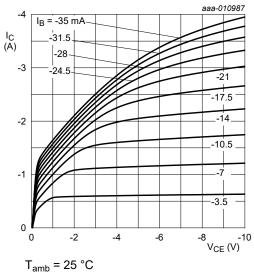
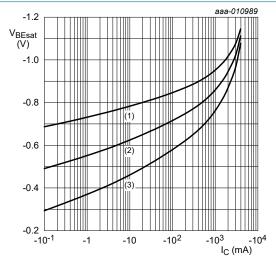


Fig. 6. Collector current as a function of collectoremitter voltage; typical values



 $I_{\rm C}/I_{\rm B}=20$ 

(1)  $T_{amb} = -55$  °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

#### 140 V, 4 A PNP high-voltage low VCEsat transistor

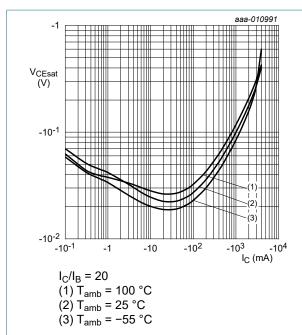


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

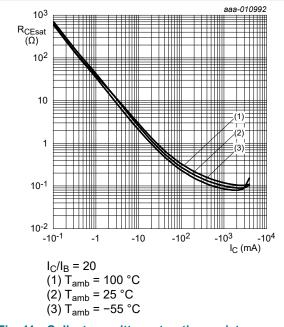


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

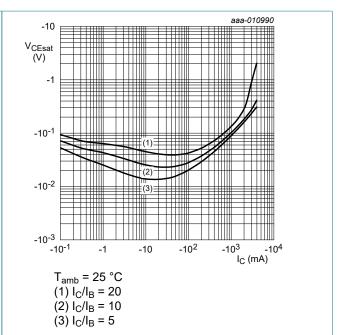


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

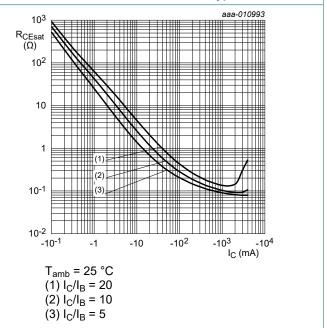


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

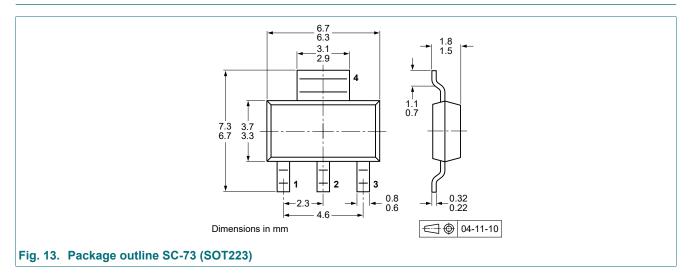
### 11. Test information

## **Quality information**

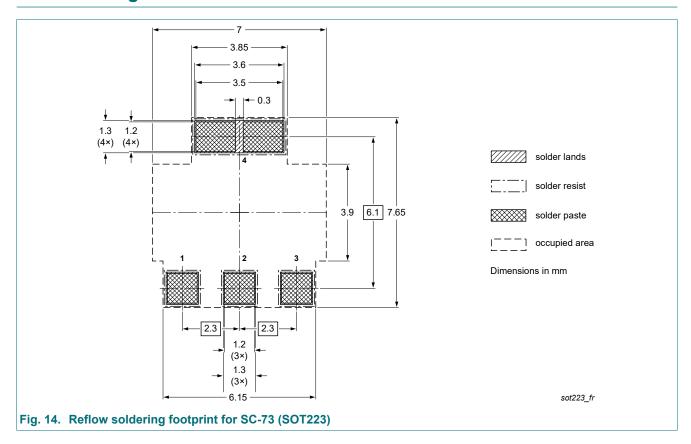
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

140 V, 4 A PNP high-voltage low VCEsat transistor

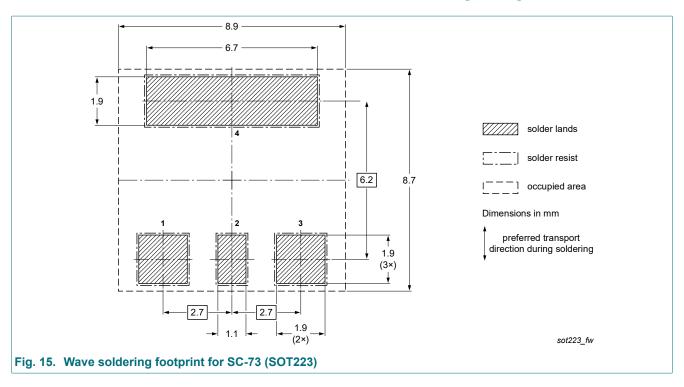
# 12. Package outline



# 13. Soldering



### 140 V, 4 A PNP high-voltage low VCEsat transistor



140 V, 4 A PNP high-voltage low VCEsat transistor

# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9414Z-Q v.1	20230717	Product data sheet	-	-

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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PBHV9414Z-Q

### 140 V, 4 A PNP high-voltage low VCEsat transistor

## **Contents**

General description	1
Features and benefits	1
Applications	1
Quick reference data	1
Pinning information	1
Ordering information	2
Marking	
Limiting values	2
Thermal characteristics	
. Characteristics	5
	Features and benefits

For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 17 July 2023

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